

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	2 x 40 A
V_{RRM}	30 V
T_{j (max)}	150 °C
V_{F (max)}	0.38 V

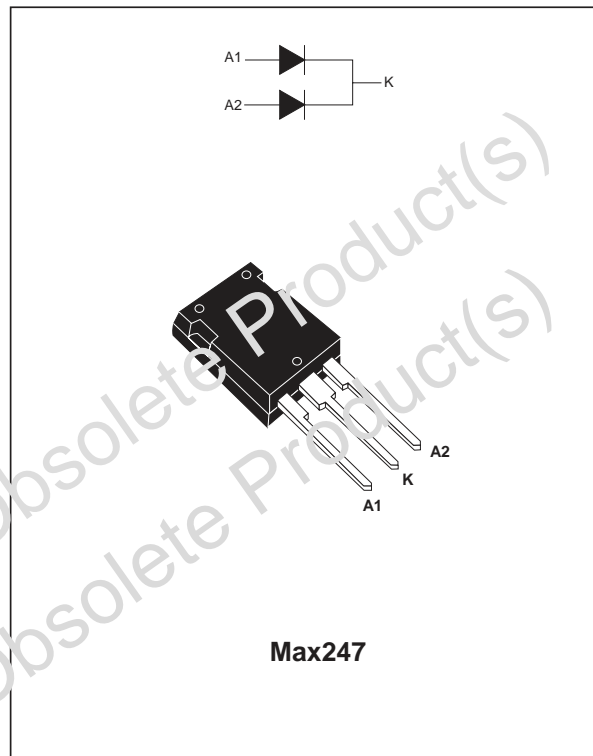
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky rectifier suited for CAD computers and servers.

Packaged in Max247, this device is intended for use in low voltage, high frequency switching power supplies, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	30	V
I _{F(RMS)}	RMS forward current	56	A
I _{F(AV)}	Average forward current	T _c = 130°C δ = 0.5 Per diode: 40 Per device: 80	A
I _{FCM}	Surge non repetitive forward current	tp = 10 ms sinusoidal	400 A
I _{RRM}	Repetitive peak reverse current	tp = 2 μs F = 1kHz square	2 A
P _{ARM}	Repetitive peak avalanche power	tp = 1 μs T _j = 25°C	13000 W
T _{stg}	Storage temperature range	- 55 to + 150	°C
T _j	Maximum operating junction temperature	150	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS80L30CY

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.7	$^{\circ}\text{C/W}$
		Total	0.5	
$R_{th(c)}$		Coupling	0.3	

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			4	μA
		$T_j = 125^{\circ}\text{C}$		0.7	1.5		
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 40\text{ A}$			0.43	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 40\text{ A}$		0.34	0.38	
		$T_j = 25^{\circ}\text{C}$	$I_F = 80\text{ A}$			0.58	
		$T_j = 125^{\circ}\text{C}$	$I_F = 80\text{ A}$	0.48	0.53		

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :
 $P = 0.23 \times I_{F(AV)} + 0.0037 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode).

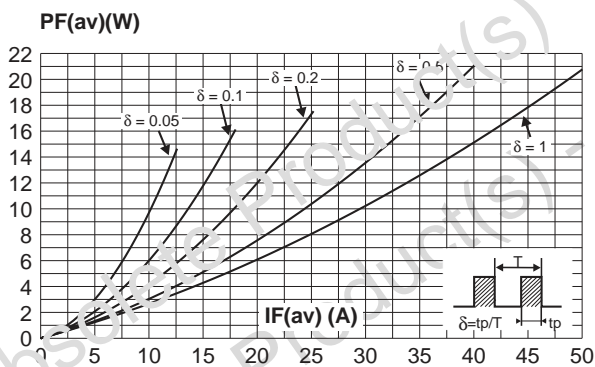


Fig. 3: Normalized avalanche power derating versus pulse duration.

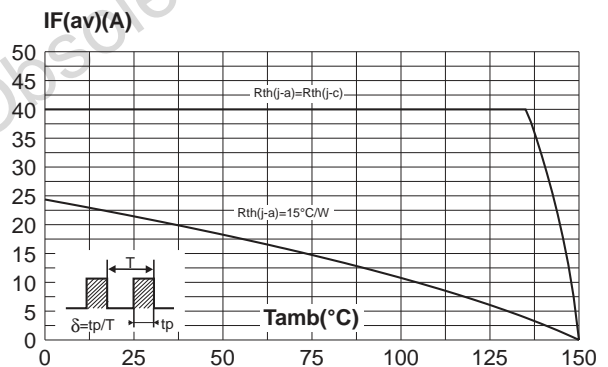


Fig. 4: Normalized avalanche power derating versus junction temperature.

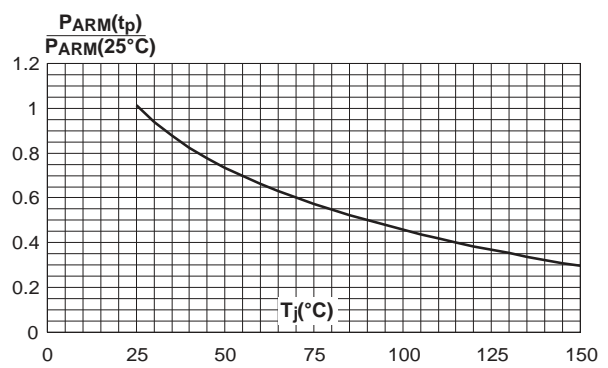
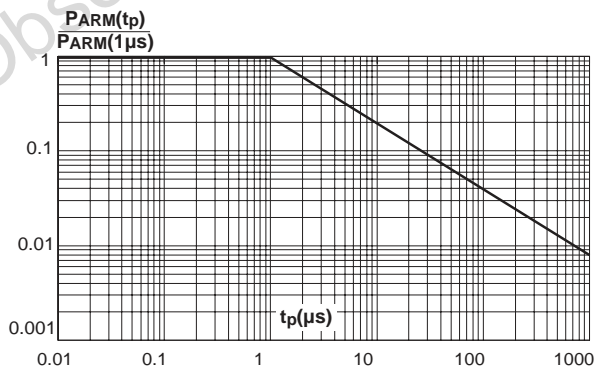


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

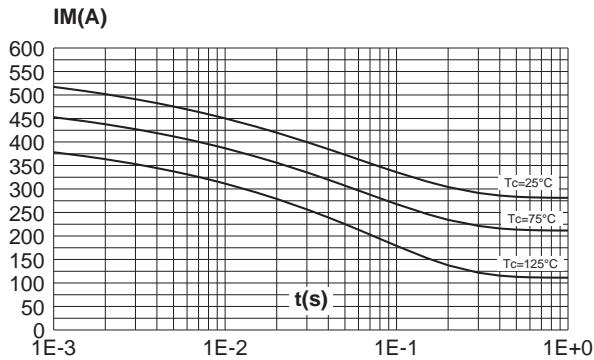


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

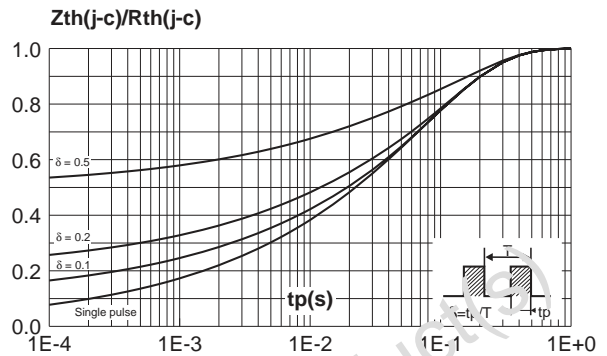


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

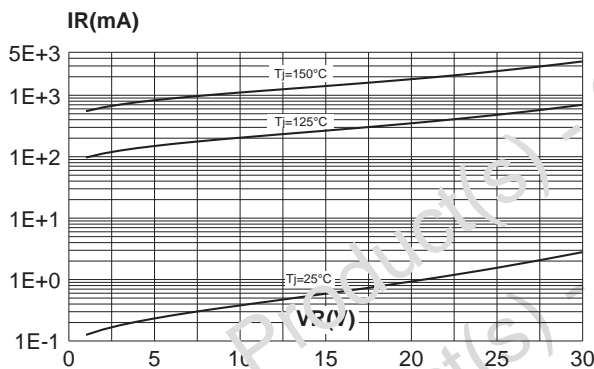


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

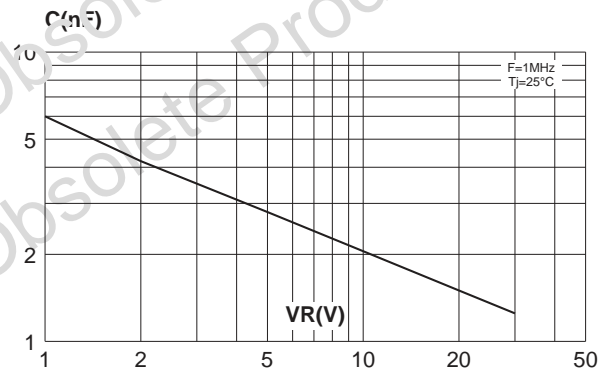
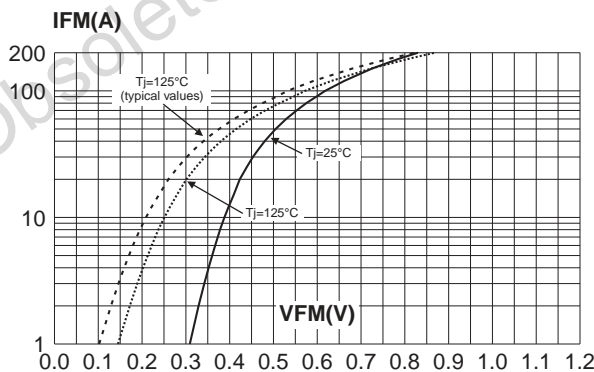
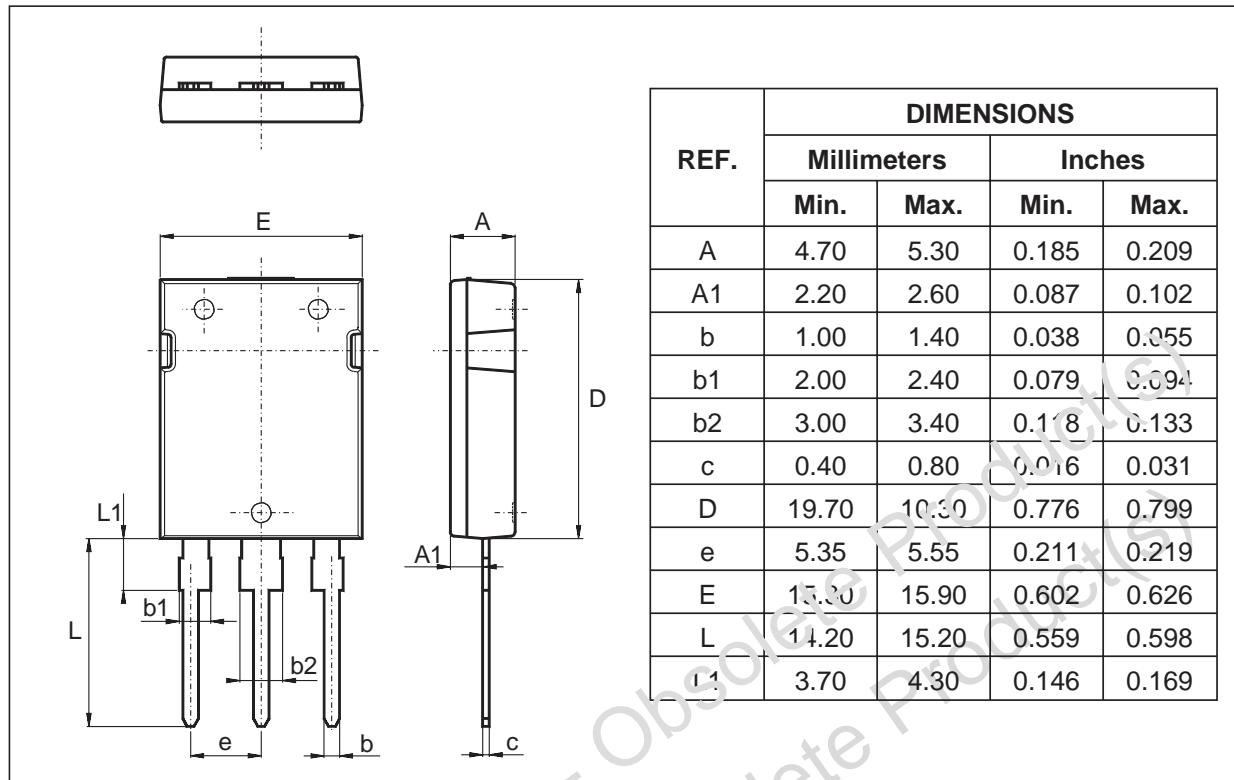


Fig. 9: Forward voltage drop versus forward current (maximum values, per diode).



STPS80L30CY

PACKAGE MECHANICAL DATA Max247



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS80L30CY	STPS80L30CY	Max247	4.4 g	30	Tube

- EPOXY MEETS UL94 V0
- COOLING METHOD: C

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